

600V, 15A, Trench FS II IGBT

General Description:

Using WOS's proprietary trench design and advanced FS (field stop) second generation technology, the 600V Trench FS II IGBT offers superior conduction and switching performances, and easy parallel operation;

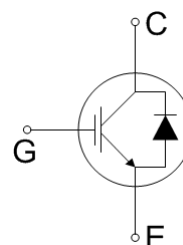
Features

Trench FSII Technology offering

- Very low $V_{CE(sat)}$
- High speed switching
- Positive temperature coefficient in $V_{CE(sat)}$
- Very tight parameter distribution
- High ruggedness, temperature stable behavior

Application

- Air Condition
- Inverters
- Motor drives



Schematic diagram

Package Marking and Ordering Information

Device	Device Package	Device Marking
PGB15TD60	TO-263	PGB15TD60
PGP15TD60	TO-220	PGP15TD60
PGF15TD60	TO-220F	PGF15TD60



TO-263



TO-220



TO-220F

Absolute Maximum Ratings (TC=25°C unless otherwise noted)

Symbol	Parameter	PGB15TD60 PGP15TD60	PGF15TD60	Units
V_{CES}	Collector-Emitter Voltage	600		V
V_{GES}	Gate- Emitter Voltage	± 30		V
I_C	Collector Current	30	30*	A
	Collector Current @ $T_C = 100^\circ\text{C}$	15	15*	A
I_{Cplus}	Pulsed Collector Current, t_p limited by T_{jmax}	45	45	A
-	turn off safe operating area, $V_{CE}=600\text{V}$, $T_j=150^\circ\text{C}$	45	45	A
I_F	Diode Continuous Forward Current @ $T_C = 100^\circ\text{C}$	15	15*	A
I_{FM}	Diode Maximum Forward Current	45	45	A
P_D	Power Dissipation @ $T_C = 25^\circ\text{C}$	105	35	W
	Power Dissipation @ $T_C = 100^\circ\text{C}$	42	12.8	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	-55 to +150		$^\circ\text{C}$
T_L	Maximum Temperature for Soldering	260		$^\circ\text{C}$
t_{sc}	Short circuit withstand time $V_{GE}=15.0\text{V}$, $V_{CC} \leq 400\text{V}$, Allowed number of short circuits < 1000 Time between short circuits: $\geq 1.0\text{s}$, $T_j \leq 150^\circ\text{C}$	10		μs

Thermal Characteristic

Symbol	Parameter	PGB15TD60 PGP15TD60	PGF15TD60	Units
$R_{\theta JC}$	Thermal Resistance, Junction to case for IGBT	1.19	3.6	$^{\circ}\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction to case for Diode	1.92	3.9	$^{\circ}\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62	78	$^{\circ}\text{C/W}$

Electrical Characteristics ($T_c=25^{\circ}\text{C}$ unless otherwise noted)

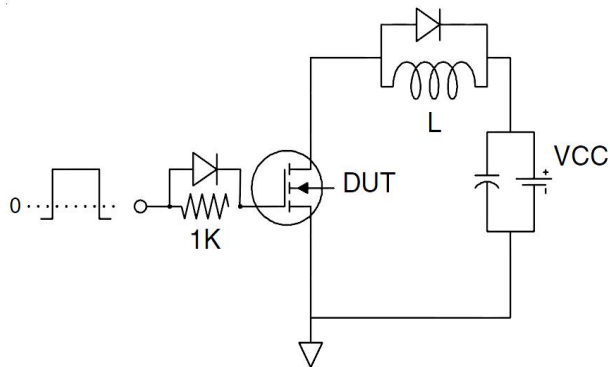
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
OFF Characteristics						
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	$V_{GE}=0V, I_{CE}=1mA$	600	--	--	V
I_{CES}	Collector-Emitter Leakage Current	$V_{GE}=0V, V_{CE}=600V$	--	--	4	μA
$I_{GES(F)}$	Gate to Emitter Forward Leakage	$V_{GE}=+30V, V_{CE}=0V$	--	--	100	nA
$I_{GES(R)}$	Gate to Source Reverse Leakage	$V_{GE}=-30V, V_{CE}=0V$	--	--	100	nA
ON Characteristics						
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=15A, V_{GE}=15V$	--	1.8	2.0	V
$V_{GE(th)}$	Gate Threshold Voltage	$I_C=1mA, V_{CE}=V_{GE}$	4.0	5.0	6.0	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	$V_{CE}=25V, V_{GE}=0V,$ $f=1MHz$	--	649	--	pF
C_{oes}	Output Capacitance		--	61	--	
C_{res}	Reverse Transfer Capacitance		--	27	--	
Q_{Gate}	Gate charge	$V_{CC}=480V, I_C=15A$ $V_{GE}=15V$	--	75	--	nC
$I_{C(SC)}$	Short circuit collector current Max.1000 short circuits Time between short circuits: $\geq 1.0s$	$V_{GE}=15V, V_{CC}\leq 400V,$ $t_{SC}\leq 10\mu s, T_j\leq 150^{\circ}C$	--	70	--	A
Switching Characteristics						
$t_{d(ON)}$	Turn-on Delay Time	$V_{CE}=400V, I_C=15A$ $V_{GE}=0/15V, R_g=15\Omega$ Inductive Load	--	17	--	ns
t_r	Rise Time		--	18	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	114	--	
t_f	Fall Time		--	41	--	
E_{on}	Turn-On Switching Loss		--	0.60	--	mJ
E_{off}	Turn-Off Switching Loss		--	0.38	--	
E_{ts}	Total Switching Loss		--	0.98	--	

Electrical Characteristics of the Diode ($T_c=25^{\circ}\text{C}$ unless otherwise specified) :

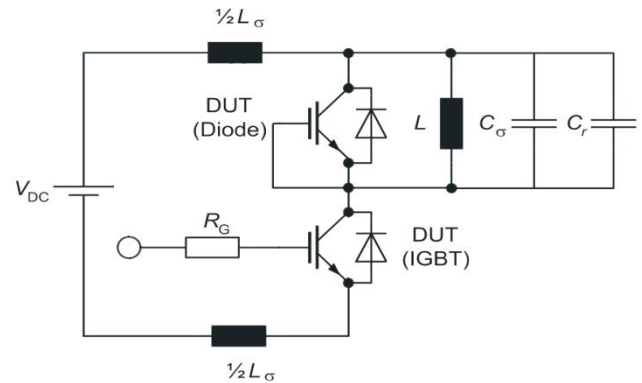
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V _{FM}	Diode Forward Voltage	I _F =15A	--	1.45	1.7	V
T _{rr}	Reverse Recovery Time	V _{cc} =400V, I _F =15A, di/dt=800A/uS	--	122	--	ns
I _{RRM}	Diode Peak Reverse Recovery Current		--	13	--	A
Q _{rr}	Reverse Recovery Charge		--	1.04	--	uC
Pulse width t _{ip} ≤380μs,δ≤2%						

Test Circuit

1) Gate Charge Test Circuit

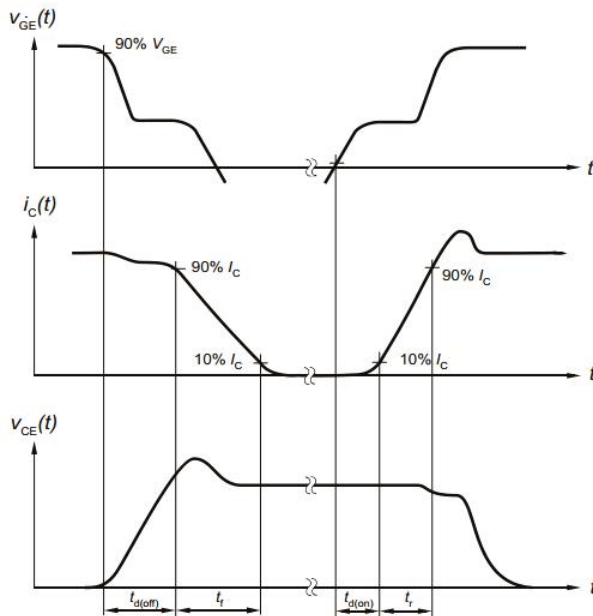


2) Switch Time Test Circuit

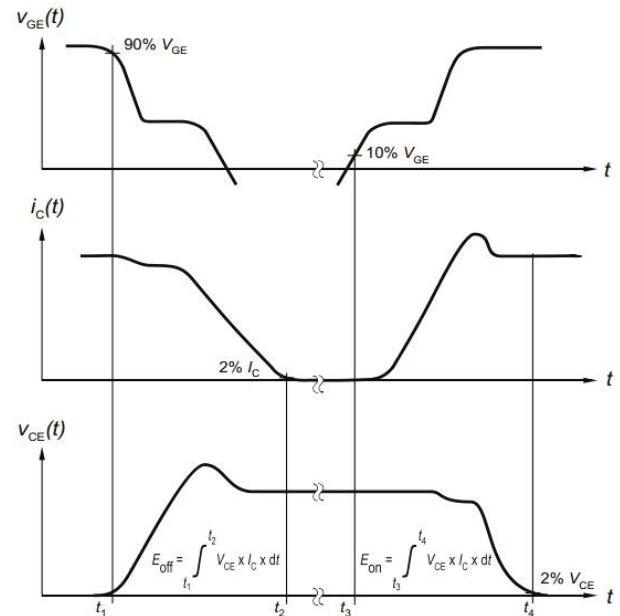


Switching characteristics

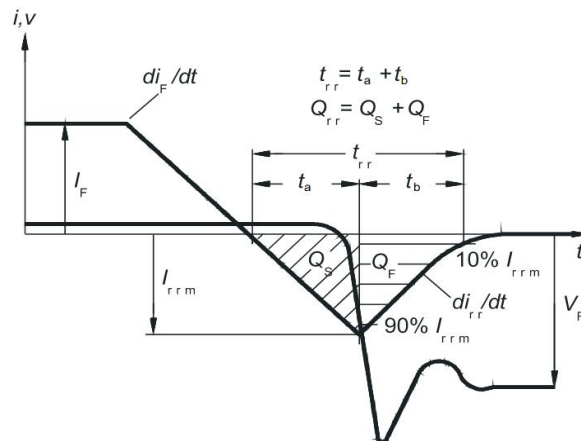
1) definition of switching times



2) definition of switching losses



3) Definition of diode switching characteristics



Typical Electrical and Thermal Characteristics

Figure 1 Output Characteristics

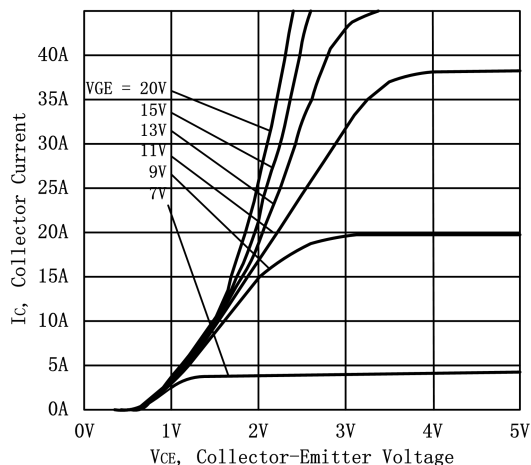


Figure 2. Transfer Characteristics

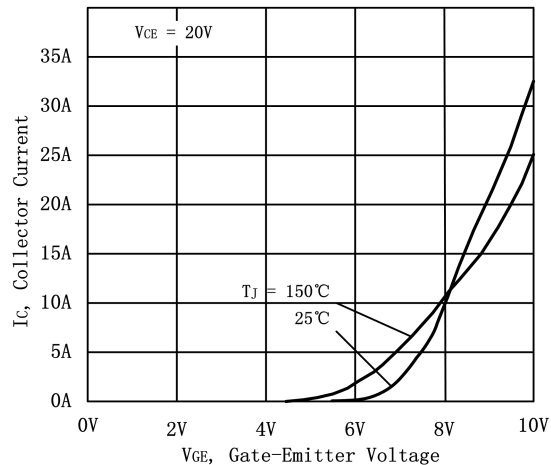


Figure 3 VCEsat vs. Case Temperature

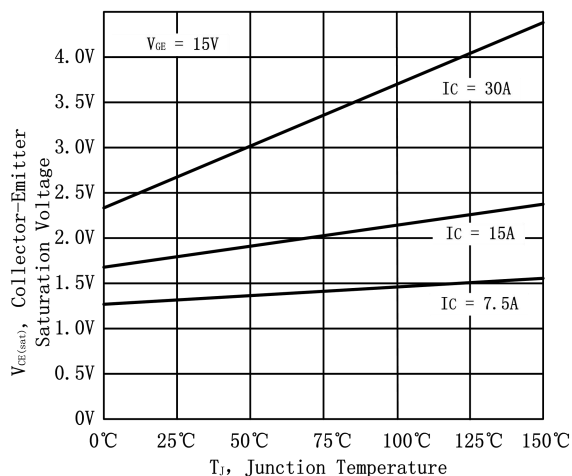


Figure 4 Saturation Voltage vs. VGE

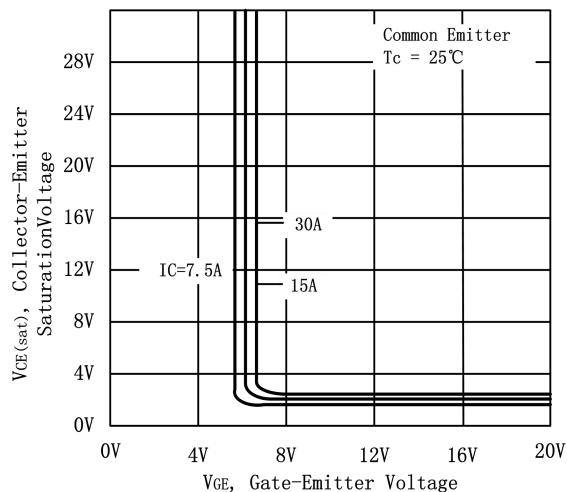


Figure 5 Capacitance Characteristics

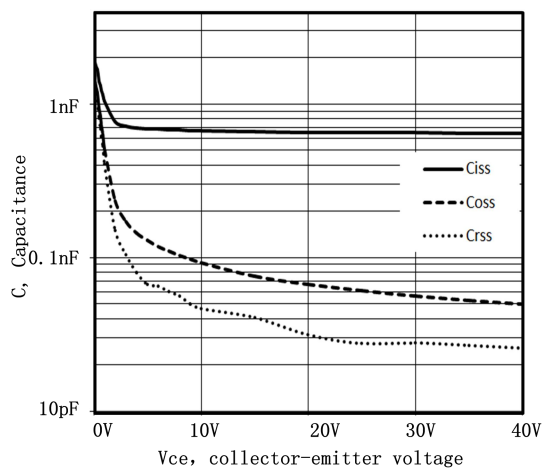
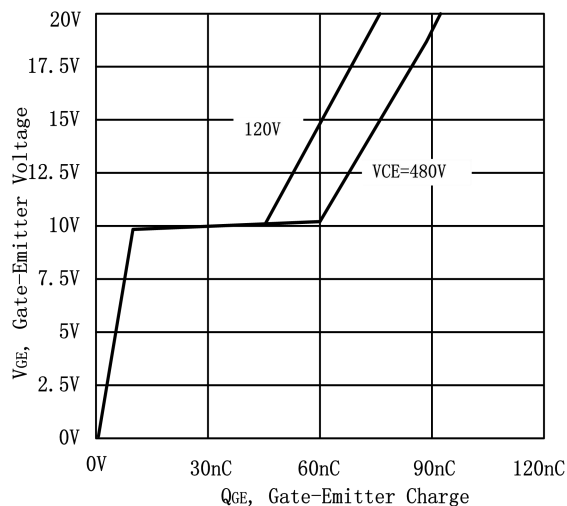


Figure 6 Gate charge waveform



Typical Electrical and Thermal Characteristics (continued)

Figure 7. Forward Characteristics

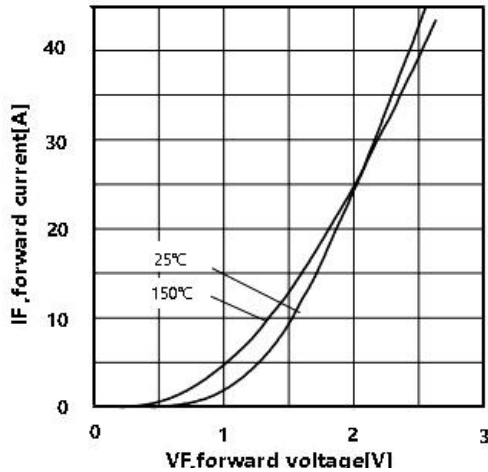


Figure 8 V_F vs. temperature

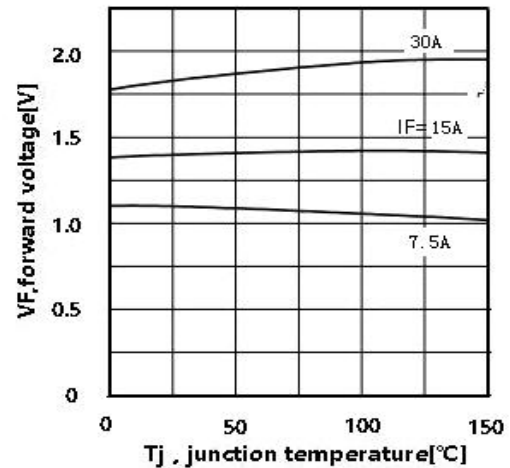


Figure 9. Transient Thermal Impedance of IGBT for TO-220F

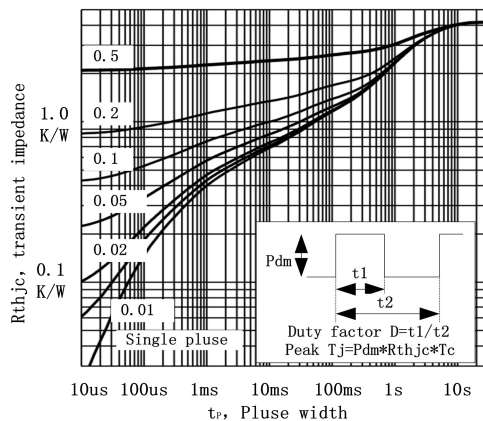


Figure 10. Transient Thermal Impedance of IGBT for TO-220, TO-263

